Photocouplers Infrared LED & Photo Darlington Transistor

TLP627M,TLP627MF

1. Applications

- Programmable Logic Controllers (PLCs)
- I/O Interface Boards
- Home Electric Appliances

2. General

TLP627M is a photocoupler that consists of an infrared emitting diode optically coupled to a photo darlington transistor. Housed in a 4pin DIP, it has a high noise immunity and high insulation. With the high breakdown voltage between the collector and emitter, TLP627M is suitable in applications such as 100 V DC output modules of programmable controllers.

TLP627MF is a lead forming type for the long creepage mounting of TLP627M.

3. Features

(1) Collector-emitter voltage: 300 V (min)

(2) Current transfer ratio: 1000 % (min) (@I_F = 1 mA, V_{CE} = 1 V)

(3) Isolation voltage: 5000 Vrms (min)

(4) Operating temperature: -55 to 110 ℃

(5) Safety standards

UL-recognized: UL 1577, File No.E67349

cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349

VDE-approved: EN IEC 60747-5-5, EN IEC 62368-1 **(Note 1)**

CQC-approved: GB4943.1 Japan Factory

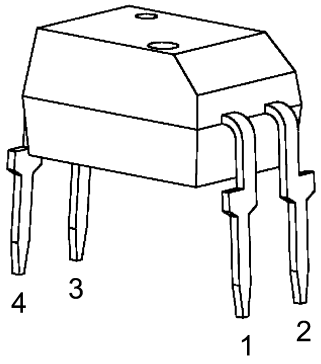
Note 1: When a VDE approved type is needed, please designate the **Option (D4)**.

Start of commercial production
2018-12

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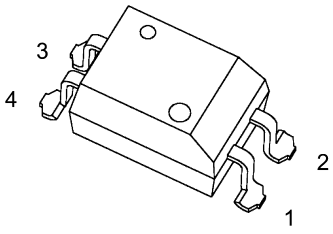
4. Packaging (Note)

TLP627M



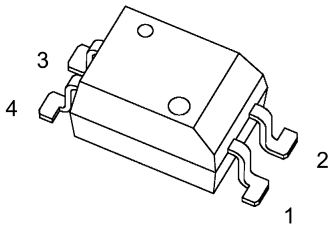
11-5B2S

TLP627M(LF1,TP1)



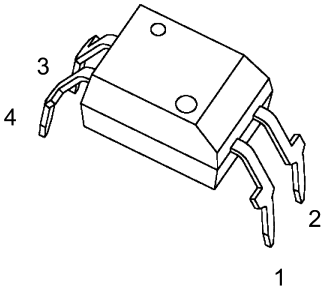
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TLP627M(LF5,TP5)



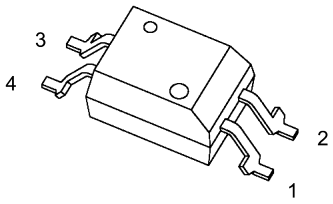
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TLP627MF



11-5B202S

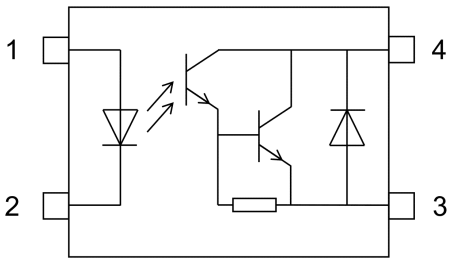
TLP627MF(LF4,TP4)



11-5B204S

Note: Through-hole type: TLP627M, TLP627MF
Lead forming option: (LF1), (LF4), (LF5)
Taping option: (TP1), (TP4), (TP5)

5. Pin Assignment



1: Anode
2: Cathode
3: Emitter
4: Collector

6. Mechanical Parameters

Characteristics	7.62 mm pitch TLP627M type (Min)	10.16 mm pitch TLP627MF type (Min)	Unit
Creepage distances	7.0	8.0	mm
Clearance	7.0	8.0	
Internal isolation thickness	0.4	0.4	

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7. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C)

	Characteristics		Symbol	Note	Rating	Unit
LED	Input forward current		I_F		50	mA
	Input forward current derating	($T_a \geq$ 90 °C)	$\Delta I_F/\Delta T_a$		-1.42	mA/°C
	Input forward current (pulsed)		I_{FP}	(Note 1)	1	A
	Input reverse voltage		V_R		5	V
	Input power dissipation		P_D		100	mW
	Input power dissipation derating	($T_a \geq$ 90 °C)	$\Delta P_D/\Delta T_a$		-2.85	mW/°C
	Junction temperature		T_j		125	°C
Detector	Collector-emitter voltage		V_{CEO}		300	V
	Emitter-collector voltage		V_{ECO}		0.3	V
	Collector current		I_C		150	mA
	Collector power dissipation		P_C		150	mW
	Collector power dissipation derating	($T_a \geq$ 25 °C)	$\Delta P_C/\Delta T_a$		-1.5	mW/°C
	Junction temperature		T_j		125	°C
Common	Operating temperature		T_{opr}		-55 to 110	°C
	Storage temperature		T_{stg}		-55 to 125	°C
	Lead soldering temperature	(10 s)	T_{sol}		260	°C
	Total power dissipation		P_T		250	mW
	Total power dissipation derating	($T_a \geq$ 25 °C)	$\Delta P_T/\Delta T_a$		-2.5	mW/°C
	Isolation voltage	(AC, 60 s, R.H. ≤ 60 %)	BV_S	(Note 2)	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW) ≤ 0.1 ms, f = 100 Hz

Note 2: This device is considered as a two-terminal device: Pins 1 and 2 are shorted together, and pins 3 and 4 are shorted together.

8. Electrical Characteristics (Unless otherwise specified, T_a = 25 °C)

	Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
LED	Input forward voltage	V_F		I_F = 10 mA	1.1	1.25	1.4	V
	Input reverse current	I_R		V_R = 5 V	—	—	10	μA
	Input capacitance	C_t		V = 0 V, f = 1 MHz	—	30	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$		I_C = 0.1 mA	300	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR)ECO}$		I_E = 0.1 mA	0.3	—	—	V
	Dark Current	I_{DARK}		V_{CE} = 200 V	—	0.002	0.2	μA
				V_{CE} = 200 V, T_a = 85 °C	—	—	20	
	Collector-emitter capacitance	C_{CE}		V = 0 V, f = 1 MHz	—	900	—	pF

9. Coupled Electrical Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Current transfer ratio	I_C/I_F		I_F = 1 mA, V_{CE} = 1 V	1000	6000	—	%
Saturated current transfer ratio	$I_C/I_{F(sat)}$		I_F = 10 mA, V_{CE} = 1 V	500	—	—	%
Collector-emitter saturation voltage	$V_{CE(sat)}$		I_C = 10 mA, I_F = 1 mA	—	—	1.0	V
			I_C = 100 mA, I_F = 10 mA	0.3	—	1.2	
OFF-state collector current	$I_{C(off)}$		V_F = 0.7 V, V_{CE} = 200 V	—	—	20	μA

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10. Isolation Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Total capacitance (input to output)	C_S	(Note 1)	V_S = 0 V, f = 1 MHz	—	0.6	—	pF
Isolation resistance	R_S	(Note 1)	V_S = 500 V, R.H. ≤ 60 %	1×10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	(Note 1)	AC, 60 s	5000	—	—	Vrms

Note 1: This device is considered as a two-terminal device: Pins 1 and 2 are shorted together, and pins 3 and 4 are shorted together.

11. Switching Characteristics (Unless otherwise specified,T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Rise time	t_r		V_{CC} = 10 V, I_C = 10 mA, R_L = 100 Ω	—	60	—	μs
Fall time	t_f			—	30	—	
Turn-on time	t_{on}			—	110	—	
Turn-off time	t_{off}			—	30	—	
Turn-on time	t_{on}		See Fig. 11.1. R_L = 180 Ω, V_{CC} = 10 V, I_F = 16 mA	—	2	—	
Storage time	t_s			—	25	—	
Turn-off time	t_{off}			—	80	—	

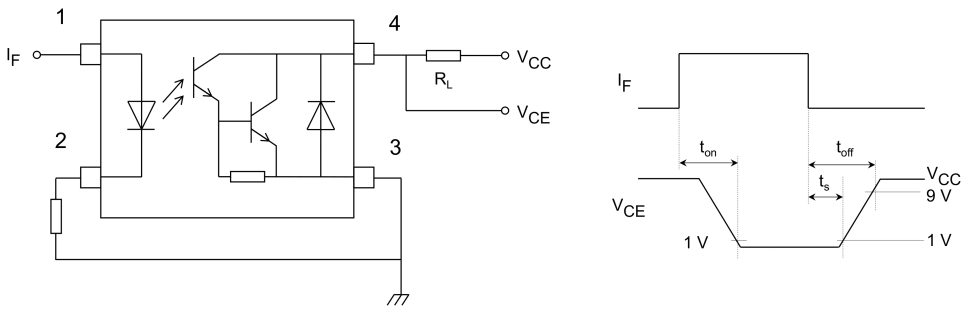


Fig. 11.1 Switching Time Test Circuit and Waveform

12. Characteristics Curves (Note)

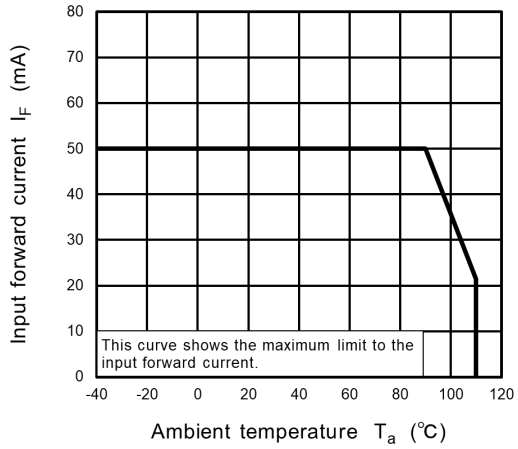


Fig. 12.1 I_F - T_a

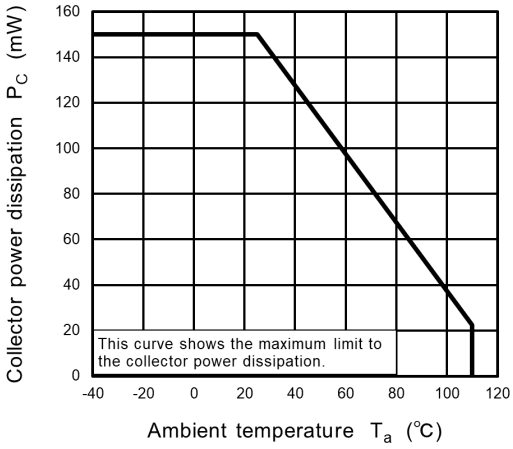


Fig. 12.2 P_C - T_a

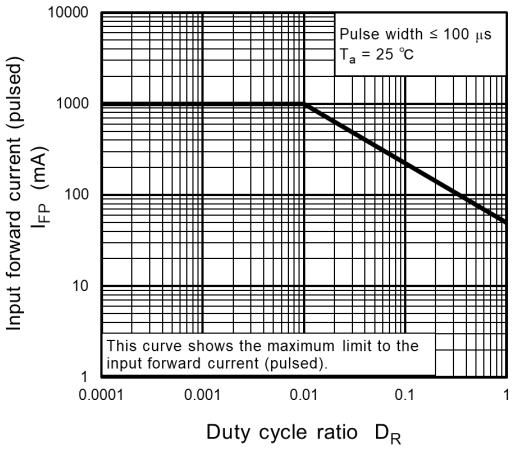


Fig. 12.3 I_{FP} - D_R

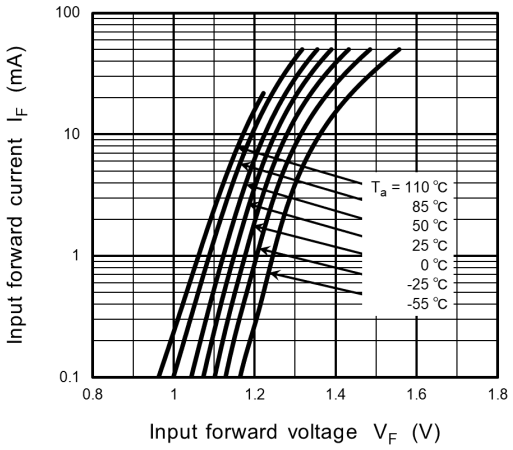


Fig. 12.4 I_F - V_F

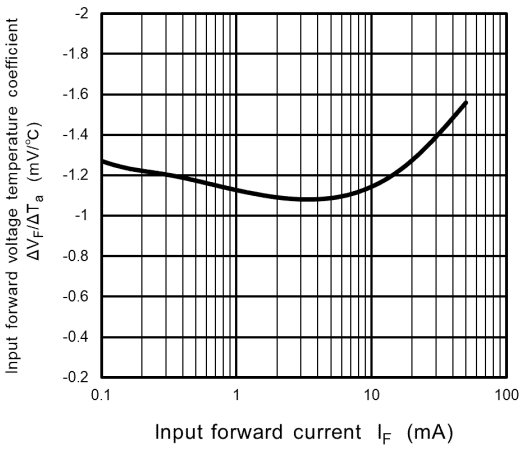


Fig. 12.5 $\Delta V_F/\Delta T_a$ - I_F

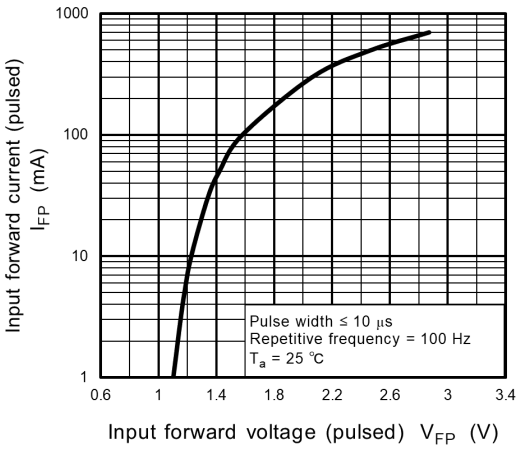


Fig. 12.6 I_{FP} - V_{FP}

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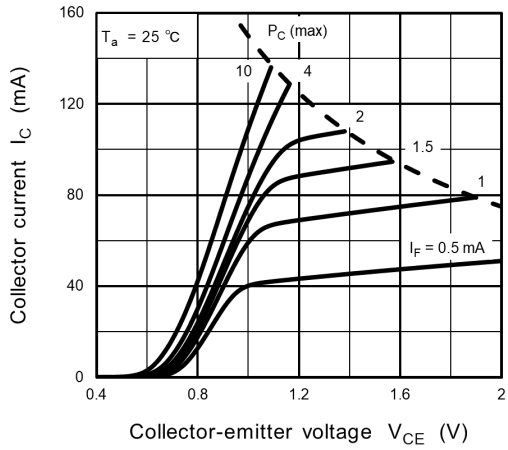


Fig. 12.7 I_C - V_{CE}

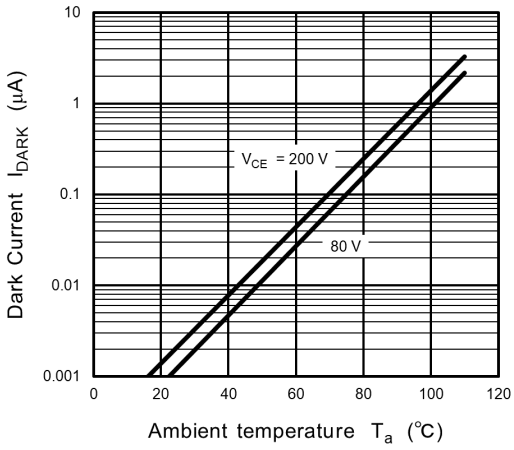


Fig. 12.8 I_{DARK} - T_a

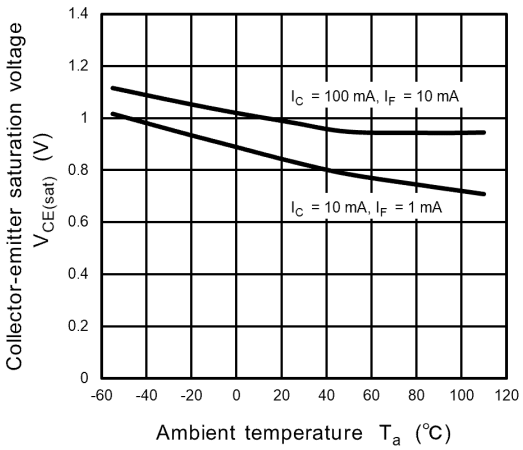


Fig. 12.9 $V_{CE(sat)}$ - T_a

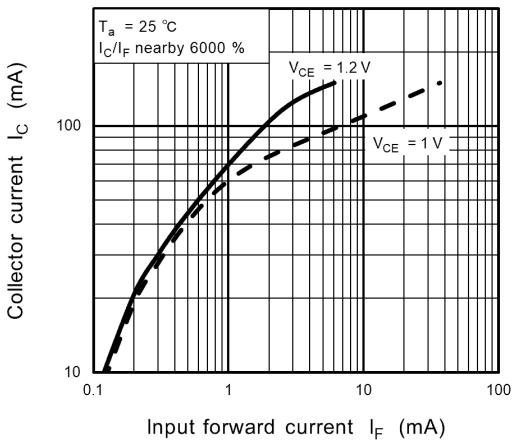


Fig. 12.10 I_C - I_F

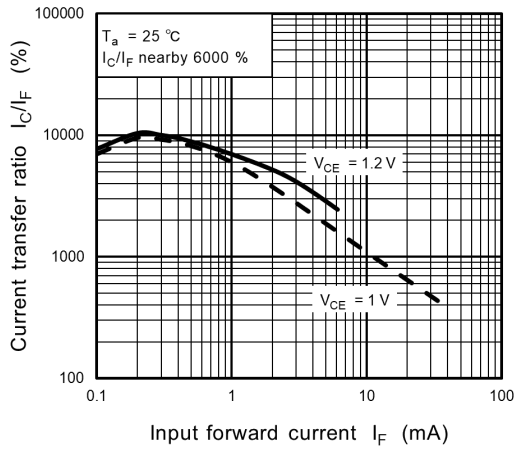


Fig. 12.11 I_C/I_F - I_F

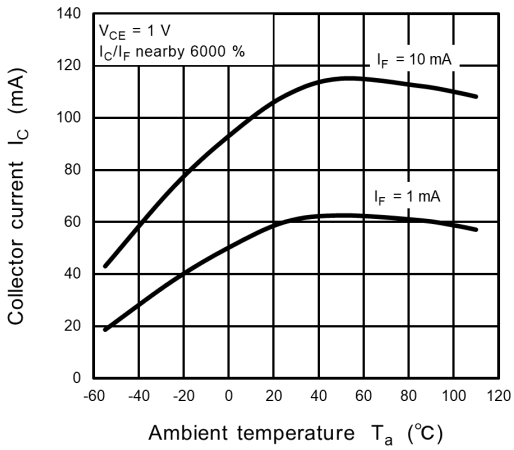


Fig. 12.12 I_C - T_a

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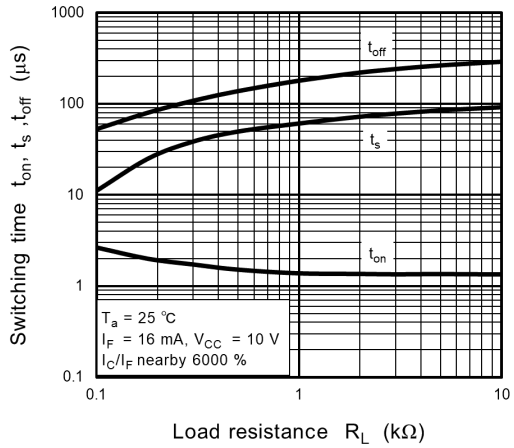


Fig. 12.13 Switching Time - R_L

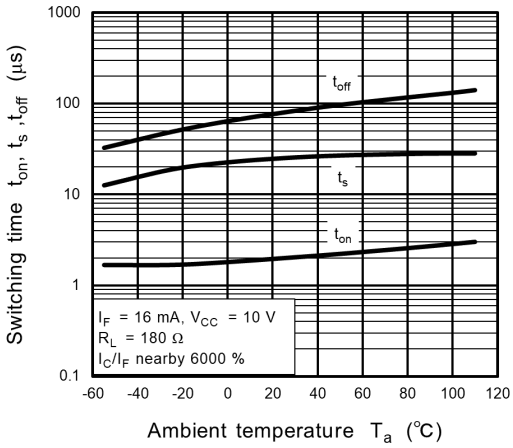


Fig. 12.14 Switching Time - T_a

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

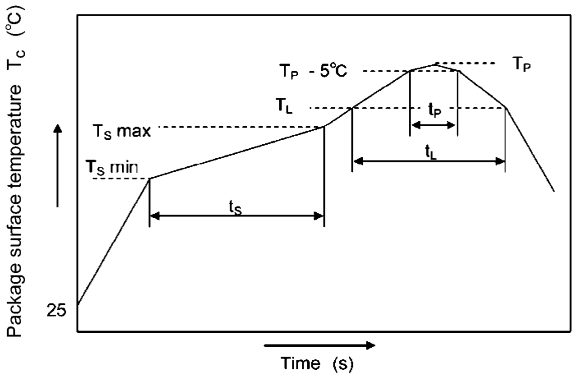
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13. Soldering and Storage

13.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

- When using soldering reflow.
  The soldering temperature profile is based on the package surface temperature.
  (See the figure shown below, which is based on the package surface temperature.)
  Reflow soldering must be performed once or twice.
  The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	T_S	150	200	°C
Preheat time	t_S	60	120	s
Ramp-up rate (T_L to T_P)			3	°C/s
Liquidus temperature	T_L	217		°C
Time above T_L	t_L	60	150	s
Peak temperature	T_P		260	°C
Time during which T_c is between (T_P – 5) and T_P	t_P		30	s
Ramp-down rate (T_P to T_L)			6	°C/s

An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

- When using soldering flow
  Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds.
  Mounting condition of 260 °C within 10 seconds is recommended.
  Flow soldering must be performed once.
- When using soldering Iron
  Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C
  Heating by soldering iron must be done only once per lead.

13.2. Precautions for General Storage

- Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the devices in locations with poisonous gases (especially corrosive gases) or in dusty conditions.

- Store the devices in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.

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14. Marking (Note)

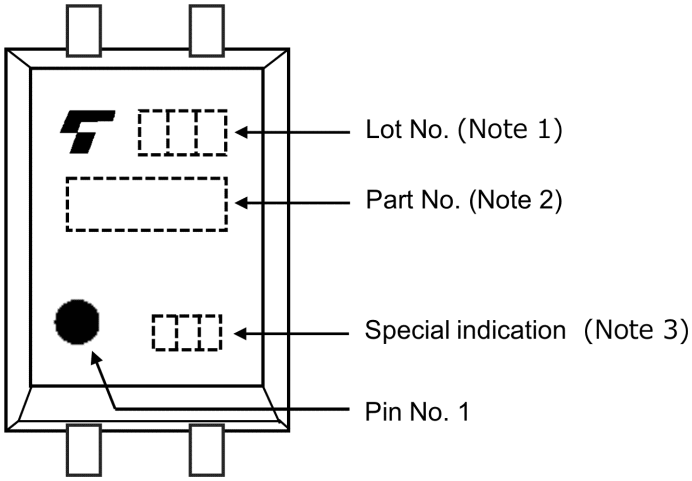


Fig. 14.1 Marking example of TLP627M

Note 1: If the lot number is expressed with three characters, it indicates "manufacturing year (1 character) + manufacturing week (2 characters)".
For example, if the lot number shown on the product is "841", it means the product was manufactured in the 41st week of a year ending in 8.

Note 2: P627M (Abbreviation code), P627MF (Abbreviation code)

Note 3: Special indication is put for the traceability enhancement.
Information of special indication
e.g. A01
A: Factory administration number
01: A counting of the number is started on every week from 01.
and reset when Lot No or weekly code is changed.

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15. EN IEC 60747-5-5 Option (D4) Specification

- Part number: TLP627M, TLP627MF **(Note 1)**
- The following part naming conventions are used for the devices that have been qualified according to option (D4) of EN IEC 60747.

  Example: TLP627M(D4-TP1,E

  D4: EN IEC 60747 option
  TP1: Tape type
  E: [[G]]/RoHS COMPATIBLE **(Note 2)**

Note 1: Use TOSHIBA standard type number for safety standard application.
e.g., TLP627M(D4-TP1,E → TLP627M

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.
RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Description		Symbol	Rating	Unit
Application classification for rated mains voltage ≤ 600 Vrms for rated mains voltage ≤ 1000 Vrms			 I-IV I-III	—
Climatic classification			55 / 110 / 21	—
Pollution degree			2	—
Maximum operating insulation voltage	TLPxxxx type	V_{IORM}	890	Vpeak
	TLPxxxxF type		1140	
Input to output test voltage, Method A V_{pr} = 1.6 × V_{IORM}, type and sample test t_p = 10 s, partial discharge < 5 pC	TLPxxxx type	V_{pr}	1424	Vpeak
	TLPxxxxF type		1824	
Input to output test voltage, Method B V_{pr} = 1.875 × V_{IORM}, 100 % production test t_p = 1 s, partial discharge < 5 pC	TLPxxxx type	V_{pr}	1670	Vpeak
	TLPxxxxF type		2140	
Highest permissible overvoltage (transient overvoltage, t_{pr} = 60 s)		V_{TR}	8000	Vpeak
Safety limiting values (max. permissible ratings in case of fault, also refer to thermal derating curve) current (input current I_F, P_{so} = 0) power (output or total power dissipation) temperature		 I_{si} P_{so} T_s	 400 700 150	 mA mW °C
Insulation resistance	V_{IO} = 500 V, T_a = 25 °C V_{IO} = 500 V, T_a = 100 °C V_{IO} = 500 V, T_a = T_s	R_{si}	≥ 10^{12} ≥ 10^{11} ≥ 10^{9}	Ω

Fig. 15.1 EN IEC 60747 Insulation Characteristics

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		7.62 mm pitch TLPxxx type	10.16 mm pitch TLPxxxF type
Minimum creepage distance	Cr	7.0 mm	8.0 mm
Minimum clearance	Cl	7.0 mm	8.0 mm
Minimum insulation thickness	ti	0.4 mm	
Comparative tracking index	CTI	500	

Fig. 15.2 Insulation Related Specifications (Note)

Note: If a printed circuit is incorporated, the creepage distance and clearance may be reduced below this value. (e.g., at a standard distance between soldering eye centers of 7.5 mm). If this is not permissible, the user shall take suitable measures.

Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.

Fig. 15.3 Marking on packing for EN IEC 60747

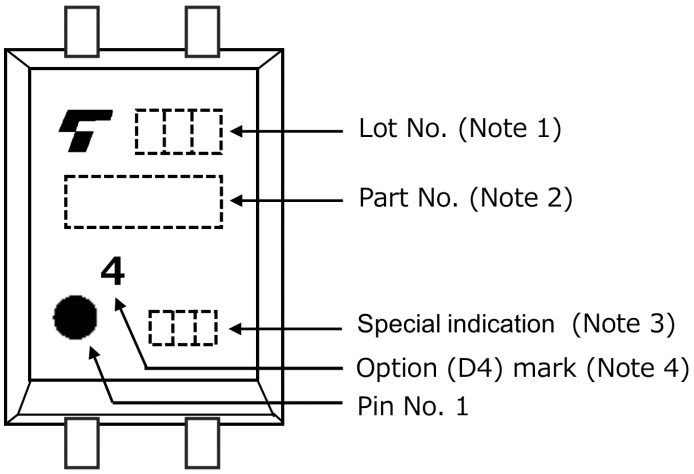


Fig. 15.4 Marking Example of TLP627M

Note 1: If the lot number is expressed with three characters, it indicates "manufacturing year (1 character) + manufacturing week (2 characters)".
For example, if the lot number shown on the product is "841", it means the product was manufactured in the 41st week of a year ending in 8.

Note 2: P627M (Abbreviation code), P627MF (Abbreviation code)

Note 3: Special indication is put for the traceability enhancement.
Information of special indication
e.g. A01
A: Factory administration number
01: A counting of the number is started on every week from 01.
and reset when Lot No or weekly code is changed.

Note 4: The above marking is applied to the photocouplers that have been qualified according to option (D4) of EN IEC 60747.

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Figure 1 Partial discharge measurement procedure according to EN IEC 60747
Destructive test for qualification and sampling tests.

Method A

(for type and sampling tests, destructive tests)

t_1, t_2	= 1 to 10 s
t_3, t_4	= 1 s
t_p (Measuring time for partial discharge)	= 10 s
t_b	= 12 s
t_{ini}	= 60 s

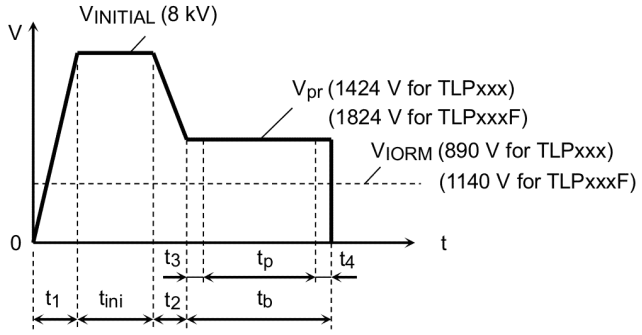


Figure 2 Partial discharge measurement procedure according to EN IEC 60747
Non-destructive test for 100 % inspection.

Method B

(for sample test, non-destructive test)

t_3, t_4	= 0.1 s
t_p (Measuring time for partial discharge)	= 1 s
t_b	= 1.2 s

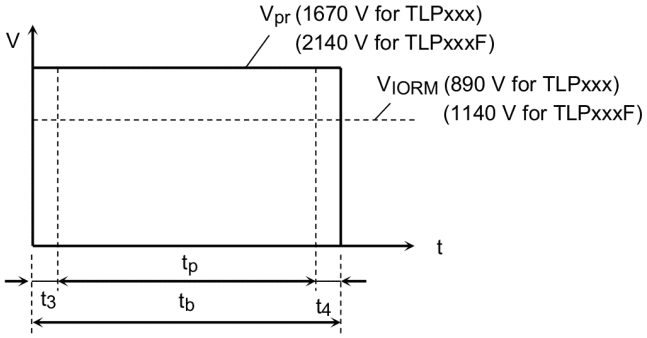


Figure 3 Dependency of maximum safety ratings on ambient temperature

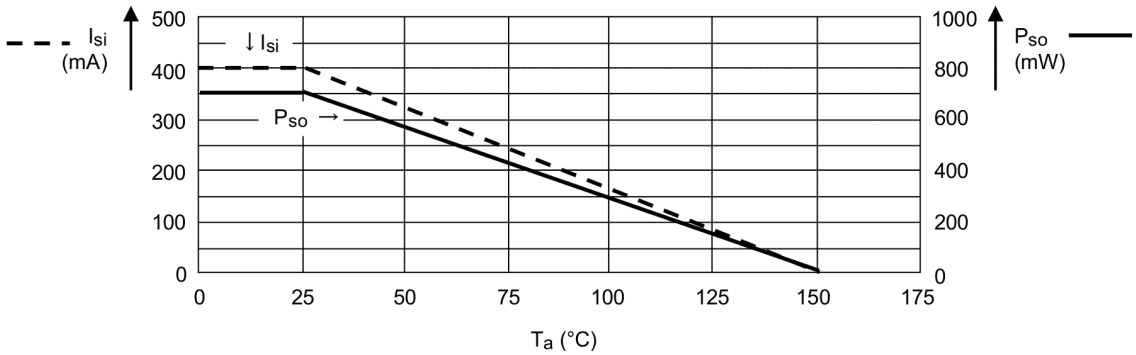


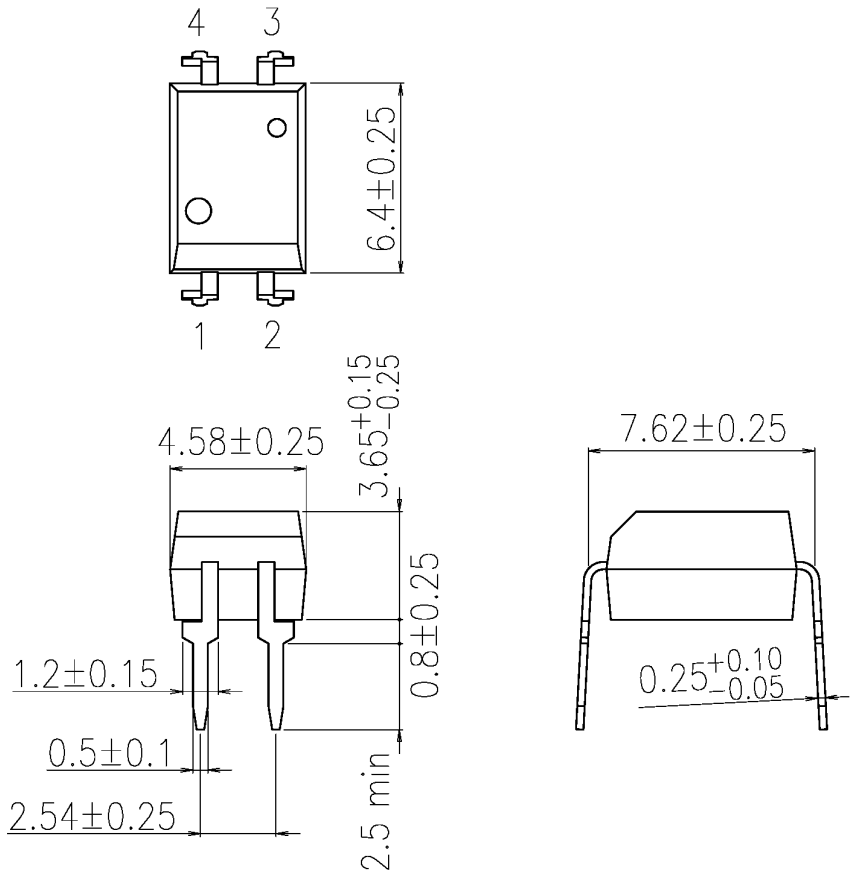
Fig. 15.5 Measurement Procedure

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Unit: mm

TLP627M



Weight: 0.24 g (typ.)

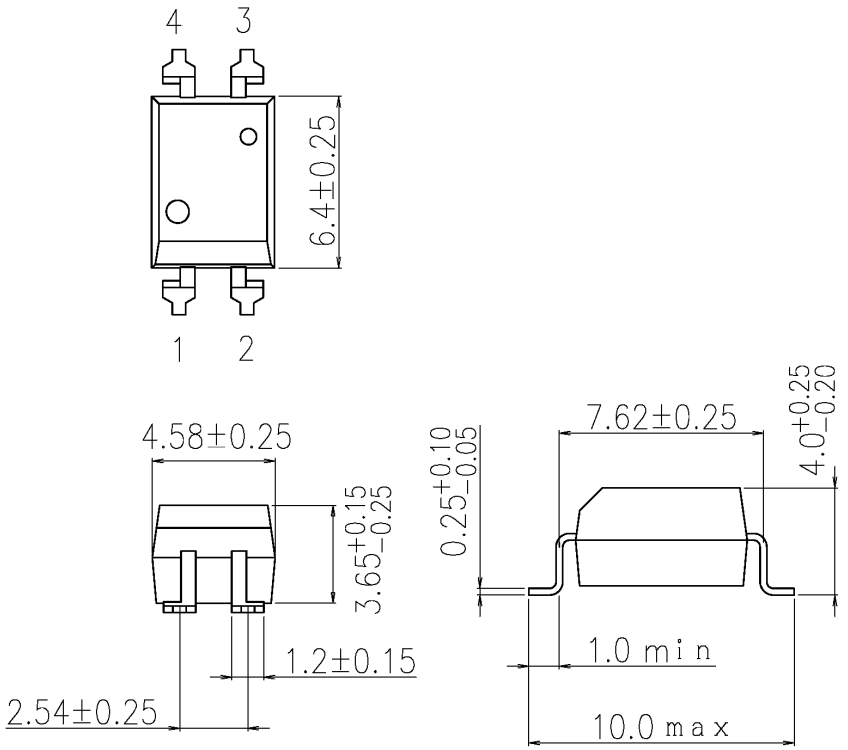
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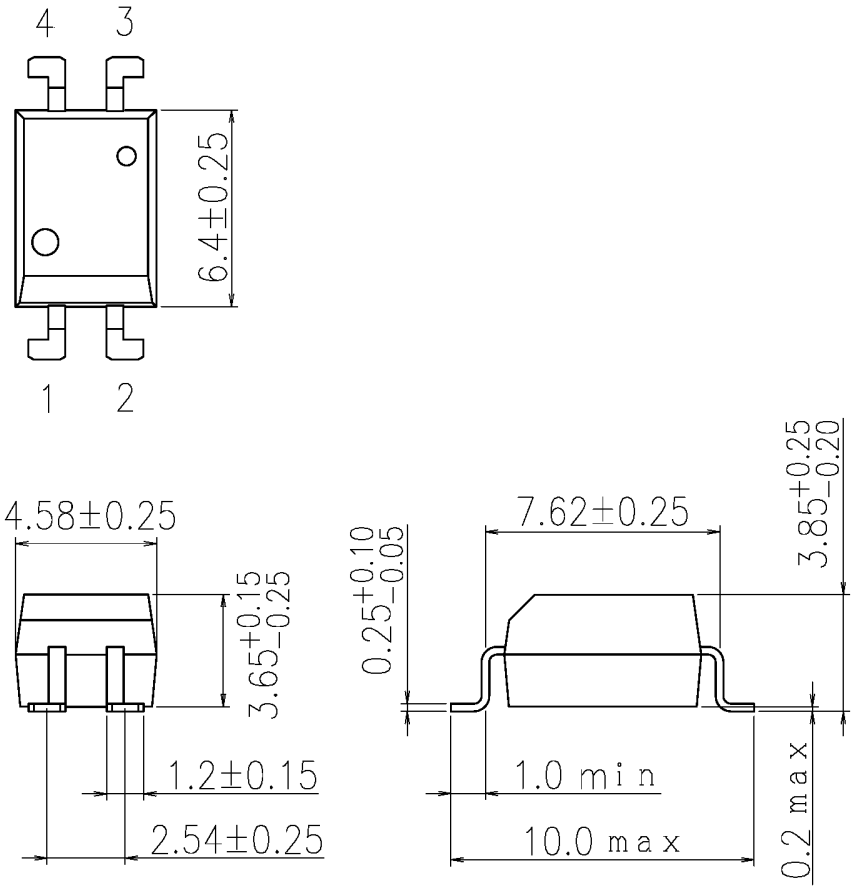
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TLP627M(LF5,TP5)



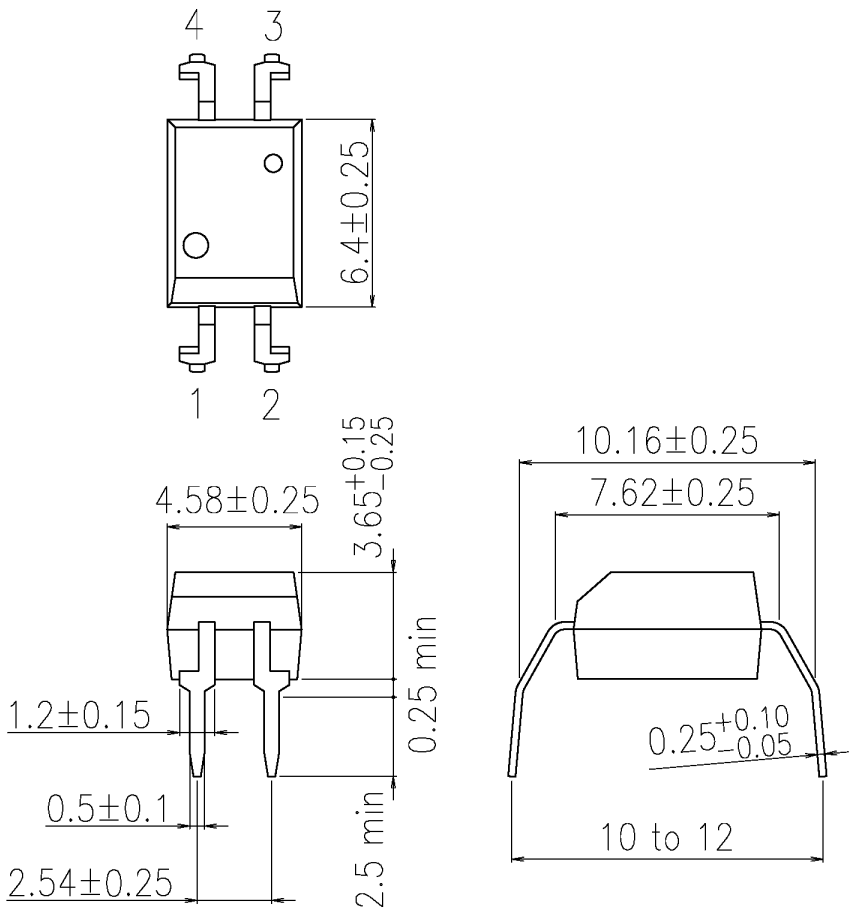
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Package Dimensions

Unit: mm

TLP627MF



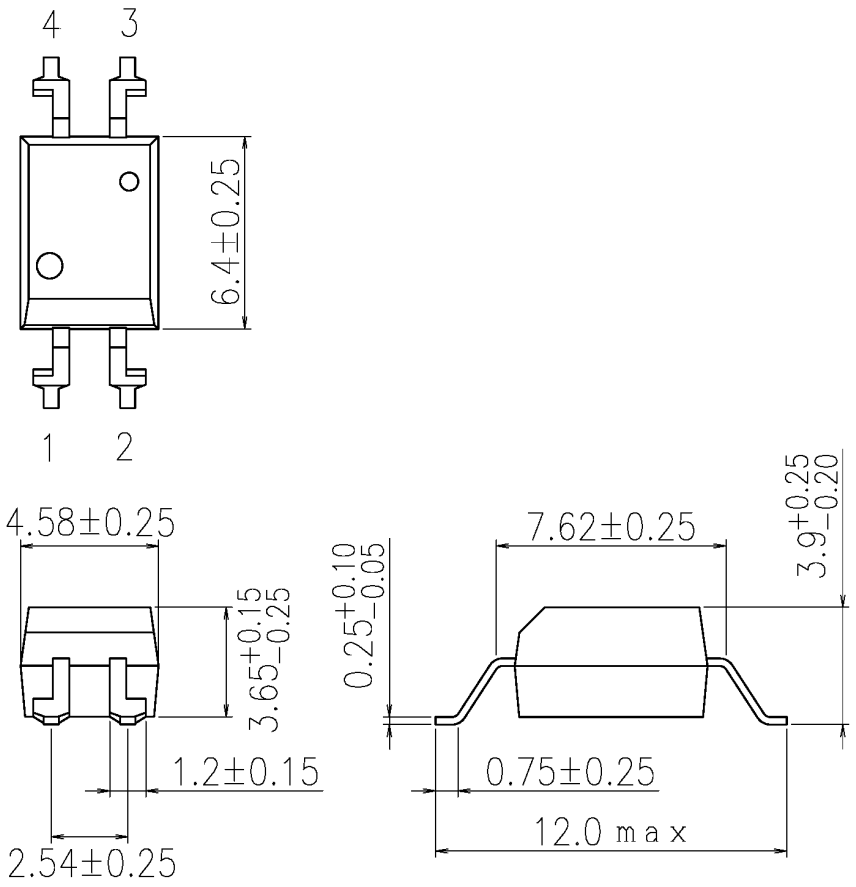
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TLP627MF(LF4,TP4)



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Package Name(s)
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